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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To manufacture a high-performance semiconductor device by preparing a semiconductor wafer suitable for a semiconductor device which has a fine structure.

CONSTITUTION: A misorientation angle of a semiconductor wafer is controlled within a specified range. Using the controlled semiconductor wafer, H₂ annealing or Ar annealing is conducted. By this method, a degree of surface flatness of the semiconductor wafer is improved. Due to the improvement of the degree of surface flatness, a voltage withholding strength of an extremely thin oxide film of a MOS device using this semiconductor wafer is increased or an yield of various types of integrated circuits, etc., is enhanced.

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